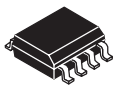


SLLS563B – JULY 2003 – REVISED DECEMBER 2003

PROFIBUS RS-485 TRANSCEIVERS

FEATURES

- **Optimized for PROFIBUS Networks**
  - **Meets the Requirements of EN 50170**
  - **Signaling Rates Up to 40 Mbps**
  - **Differential Output Exceeds 2.1 V (54 Ω Load)**
  - **Low Bus Capacitance: 10 pF (Max)**
- **Meets the Requirements of TIA/EIA-485-A**
- **ESD Protection Exceeds ±10 kV HBM**
- **Failsafe Receiver for Bus Open, Short, Idle**
- **Up to 160 Transceivers on a Bus**
- **Low Skew During Output Transitions and Driver Enabling / Disabling**
- **Common-Mode Rejection Up to 50 MHz**
- **Short-Circuit Current Limit**
- **Hot Swap Capable**
- **Thermal Shutdown Protection**

APPLICATIONS

- **Process Automation**
  - **Chemical Production**
  - **Brewing and Distillation**
  - **Paper Mills**
- **Factory Automation**
  - **Automobile Production**
  - **Rolling, Pressing, Stamping Machines**
  - **Networked Sensors**
- **General RS-485 Networks**
  - **Motor/Motion Control**
  - **HVAC and Building Automation Networks**
  - **Networked Security Stations**

DESCRIPTION

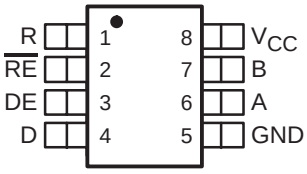
These devices are half-duplex differential transceivers, with characteristics optimized for use in PROFIBUS (EN 50170) applications. The driver output differential voltage exceeds the Profibus requirements of 2.1 V with a 54-Ω load. A signaling rate of up to 40 Mbps allows technology growth to high data transfer speeds. The low bus capacitance provides low signal distortion.

The SN65HVD1176 and SN75HVD1176 meet or exceed the requirements of ANSI standard TIA/EIA-485-A (RS-485) for differential data transmission across twisted-pair networks. The driver outputs and receiver inputs are tied together to form a half-duplex bus port, with one-fifth unit load, allowing up to 160 nodes on a single bus. The receiver output stays at logic high when the bus lines are shorted, left open, or when no driver is active. The driver outputs are in high impedance when the supply voltage is below 2.5 V to prevent bus disturbance during power cycling or during live insertion to the bus.

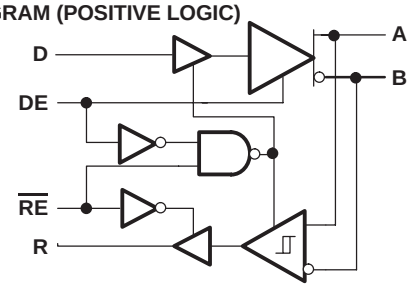
An internal current limit protects the transceiver bus pins in short-circuit fault conditions by limiting the output current to a constant value. Thermal shutdown circuitry protects the device against damage due to excessive power dissipation caused by faulty loading and drive conditions.

The SN75HVD1176 is characterized for operation at temperatures from 0°C to 70°C. The SN65HVD1176 is characterized for operation at temperatures from −40°C to 85°C.

D PACKAGE
(TOP VIEW)



LOGIC DIAGRAM (POSITIVE LOGIC)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS

T_A	PACKAGED DEVICES(1)	MARKED AS
0°C to 70°C	SN75HVD1176D	VN1176
−40°C to 85°C	SN65HVD1176D	VP1176

(1) The D package is available taped and reeled. Add an R suffix to the device type (i.e., SN65HVD1176DR).

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range unless otherwise noted(1)

			SN65HVD1176, SN75HVD1176
Supply voltage(2), V_{CC}			−0.5 V to 7 V
Voltage at any bus I/O terminal			−9 V to 14 V
Voltage input, transient pulse, A and B, (through 100 Ω, see Figure 14)			−40 V to 40 V
Voltage input at any D, DE or $\overline{RE}$ terminal			−0.5 V to 7 V
Electrostatic discharge	Human Body Model, (HBM)(3)	All pins	4 kV
		Bus terminals and GND	10 kV
Junction temperature, T_J			150°C

(1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.
(3) Tested in accordance with JEDEC standard 22. test method A114−A.

RECOMMENDED OPERATING CONDITIONS

		MIN	NOM	MAX	UNIT
Supply voltage, V_{CC}		4.75	5	5.25	V
Voltage at either bus I/O terminal	A, B	−7		12	V
High−level input voltage, V_{IH}	D, DE, $\overline{RE}$	2		V_{CC}	V
Low−level input voltage, V_{IL}	D, DE, $\overline{RE}$	0		0.8	V
Differential input voltage, V_{ID}	A with respect to B	−12		12	V
Output current	Driver	−70		70	mA
	Receiver	−8		8	mA
Junction temperature, T_J (1)	SN65HVD1176	−40		130	Ω
	SN75HVD1176	0		130	Ω
Differential load resistance, R_L		54			Ω
Signaling rate, $1/t_{U1}$				40	Mbps

(1) See the Thermal Characteristics table for more information on maintenance of this requirement.

DRIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP(1)	MAX	UNIT
V_O	Open-circuit output voltage	A or B, No load		0		V_{CC}	V
$\|V_{OD(SS)}\|$	Steady-state differential output voltage magnitude	R_L = 54 Ω, See Figure 1		2.1	2.9		V
		With common-mode loading, (V_{TEST} from −7 V to 12 V) See Figure 2		2.1	2.7		
$\Delta\|V_{OD(SS)}\|$	Change in steady-state differential output voltage between logic states	See Figure 1 and Figure 6		−0.2	0	0.2	V
$V_{OC(SS)}$	Steady-state common-mode output voltage	See Figure 5		2	2.5	3	V
$\Delta V_{OC(SS)}$	Change in steady-state common-mode output voltage			−0.2	0	0.2	V
$V_{OC(PP)}$	Peak-to-peak common-mode output voltage				0.5		V
$V_{OD(RING)}$	Differential output voltage over and under shoot	R_L = 54 Ω, C_L = 50 pF, See Figure 6				10%	$V_{OD(PP)}$
I_I	Input current	D, DE		−50		50	µA
$I_{O(OFF)}$	Output current with power off	V_{CC} < = 2.5 V		See receiver line input current			
I_{OZ}	High impedance state output current	DE at 0 V					
$I_{OS(P)}$	Peak short-circuit output current	DE at V_{CC}, See Figure 8	V_{OS} = −7 V to 12 V	−250		250	mA
$I_{OS(SS)}$	Steady-state short-circuit output current		V_{OS} > 4 V, Output driving low	60	90	135	mA
			V_{OS} < 1 V, Output driving high	−135	−90	−60	
C_{OD}	Differential output capacitance			See receiver C_I			

(1) All typical values are at V_{CC} = 5 V and 25°C.

DRIVER SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time low-level-to-high-level output	R_L = 54 Ω, C_L = 50 pF, See Figure 3		4	7	10	ns
t_{PHL}	Propagation delay time high-level-to-low-level output			4	7	10	ns
$t_{sk(p)}$	Pulse skew | $t_{PLH} - t_{PHL}$ |				0	2	ns
t_r	Differential output rise time			2	3	7.5	ns
t_f	Differential output fall time			2	3	7.5	ns
$t_{t(MLH)}$, $t_{t(MHL)}$	Output transition skew	See Figure 4			0.2	1	ns
$t_{p(AZH)}$, $t_{p(BZH)}$ $t_{p(AZL)}$, $t_{p(BZL)}$	Propagation delay time, high-impedance-to-active output	R_L = 110 Ω, C_L = 50 pF, See Figure 7a and 7b	$\overline{RE}$ at 0 V		10	20	ns
$t_{p(AHZ)}$, $t_{p(BHZ)}$ $t_{p(ALZ)}$, $t_{p(BLZ)}$	Propagation delay time, active-to- high-impedance output				10	20	ns
$\|t_{p(AZL)} - t_{p(BZH)}\|$ $\|t_{p(AZH)} - t_{p(BZL)}\|$	Enable skew time				0.55	1.5	ns
$\|t_{p(ALZ)} - t_{p(BHZ)}\|$ $\|t_{p(AHZ)} - t_{p(BLZ)}\|$	Disable skew time					2.5	ns
$t_{p(AZH)}$, $t_{p(BZH)}$ $t_{p(AZL)}$, $t_{p(BZL)}$	Propagation delay time, high-impedance-to-active output (from sleep mode)		$\overline{RE}$ at 5 V		1	4	µs
$t_{p(AHZ)}$, $t_{p(BHZ)}$ $t_{p(ALZ)}$, $t_{p(BLZ)}$	Propagation delay time, active-output-to high-impedance (to sleep mode)				30	50	ns
$t_{(CFB)}$	Time from application of short-circuit to current foldback	See Figure 8			0.5		µs
$t_{(TSD)}$	Time from application of short-circuit to thermal shutdown	T_A = 25°C, See Figure 8		100			µs

(1) All typical values are at V_{CC} = 5 V and 25°C.

RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP(1)	MAX	UNIT
$V_{IT(+)}$	Positive-going differential input voltage threshold	See Figure 9	V_O = 2.4 V, I_O = −8 mA		−80	−20	mV
$V_{IT(-)}$	Negative-going differential input voltage threshold		V_O = 0.4 V, I_O = 8 mA	−200	−120		
V_{HYS}	Hysteresis voltage ($V_{IT+} - V_{IT-}$)				40		mV
V_{OH}	High-level output voltage	V_{ID} = 200 mV, I_{OH} = −8 mA, See Figure 9		4	4.6		V
V_{OL}	Low-level output voltage	V_{ID} = −200 mV, I_{OL} = 8 mA, See Figure 9			0.2	0.4	V
I_A, I_B	Bus pin input current	V_I = − 7 V to 12 V, Other input = 0 V	V_{CC} = 4.75 V to 5.25 V	−160		200	µA
$I_{A(OFF)}$, $I_{B(OFF)}$			V_{CC} = 0V				
I_I	Receiver enable input current	$\overline{RE}$		−50		50	µA
I_{OZ}	High-impedance -state output current	$\overline{RE}$ = V_{CC}		−1		1	µA
R_I	Input resistance			60			kΩ
C_{ID}	Differential input capacitance	Test input signal is a 1.5 MHz sine wave with amplitude 1 Vpp, capacitance measured across A and B			7	10	pF
CMR	Common mode rejection	See Figure 11			4		V

(1) All typical values are at 25°C.

RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditions

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high level output	See Figure 10		20	25	ns
t_{PHL}	Propagation delay time, high-to-low level output			20	25	
$t_{sk(p)}$	Pulse skew | $t_{PLH} - t_{PHL}$ |			1	2	ns
t_r	Receiver output voltage rise time			2	4	ns
t_f	Receiver output voltage fall time			2	4	
t_{PZH}	Propagation delay time, high-impedance-to-high-level output	DE at V_{CC}, See Figure 13			20	ns
t_{PHZ}	Propagation delay time, high-level-to-high-impedance output				20	
t_{PZL}	Propagation delay time, high-impedance-to-low-level output	DE at V_{CC}, See Figure 14			20	ns
t_{PLZ}	Propagation delay time, low-level-to-high-impedance output				20	
t_{PZH}	Propagation delay time, high-impedance-to-high-level output (standby to active)	DE at 0 V, See Figure 12		1	4	µs
t_{PHZ}	Propagation delay time, high-level-to-high-impedance output (active to standby)			13	20	ns
t_{PZL}	Propagation delay time, high-impedance-to-low-level output (standby to active)	DE at 0 V See Figure 12		2	4	µs
t_{PLZ}	Propagation delay time, low-level-to-high-impedance output (active to standby)			13	20	ns

SUPPLY CURRENT

over recommended operating conditions

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{CC}	Supply current	Driver and receiver, $\overline{RE}$ at 0 V, DE at V_{CC}, All other inputs open, no load		4	6	mA
		Driver only, $\overline{RE}$ at V_{CC}, DE at V_{CC}, All other inputs open, no load		3.8	6	mA
		Receiver only, $\overline{RE}$ at 0 V, DE at 0 V, All other inputs open, no load		3.6	6	mA
		Standby only, $\overline{RE}$ at V_{CC}, DE at 0 V, All other inputs open		0.2	5	µA

PARAMETER MEASUREMENT INFORMATION

NOTES:

Test load capacitance includes probe and jig capacitance (unless otherwise specified).

Signal generator characteristics: rise and fall time < 6 ns, pulse rate 100 kHz, 50% duty cycle, Z_O = 50 Ω (unless otherwise specified)

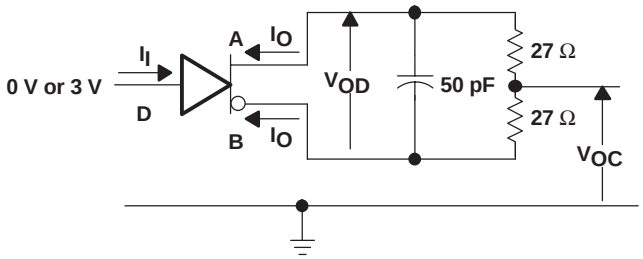


Figure 1. Driver Test Circuit, V_{OD} and V_{OC} Without Common-Mode Loading

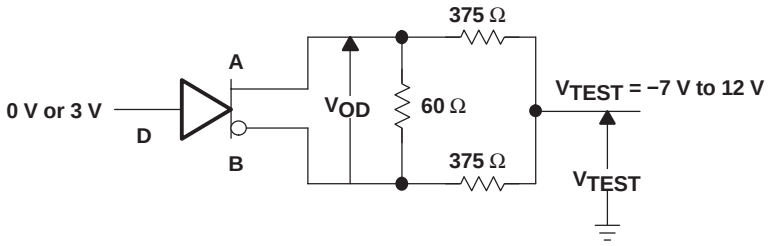


Figure 2. Driver Test Circuit, V_{OD} With Common-Mode Loading

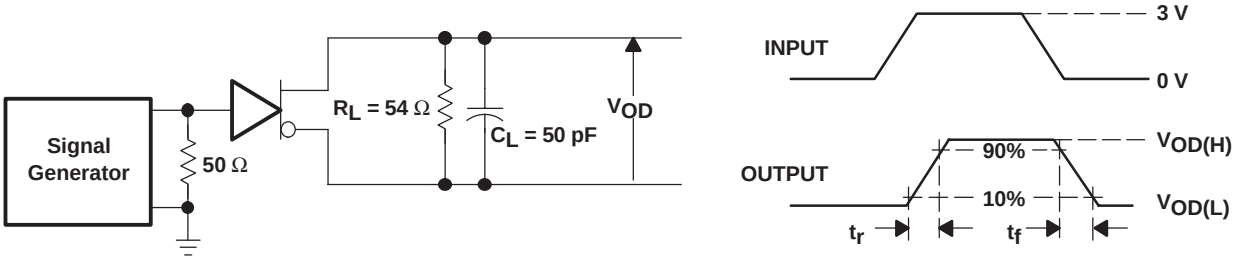


Figure 3. Driver Switching Test Circuit and Rise/Fall Time Measurement

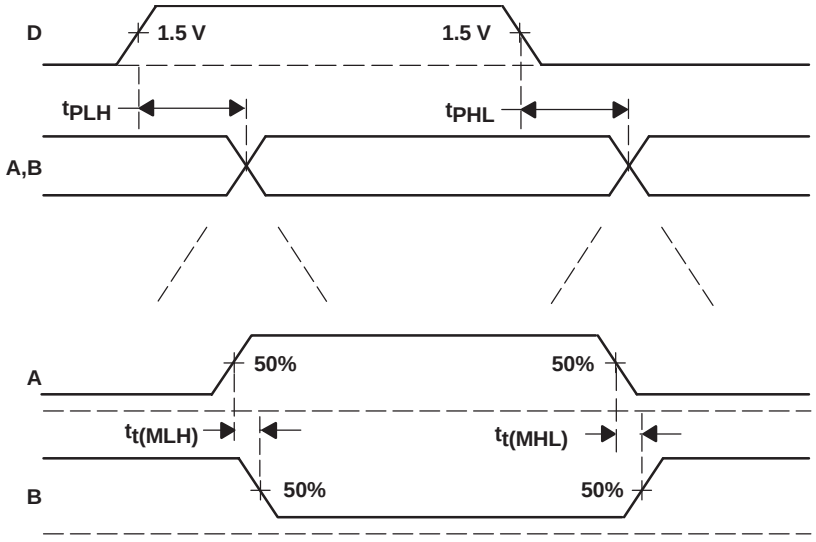


Figure 4. Driver Switching Waveforms for Propagation Delay and Output Midpoint Time Measurements

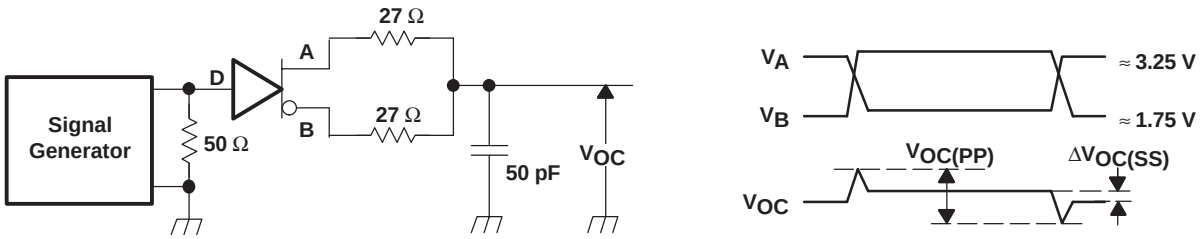
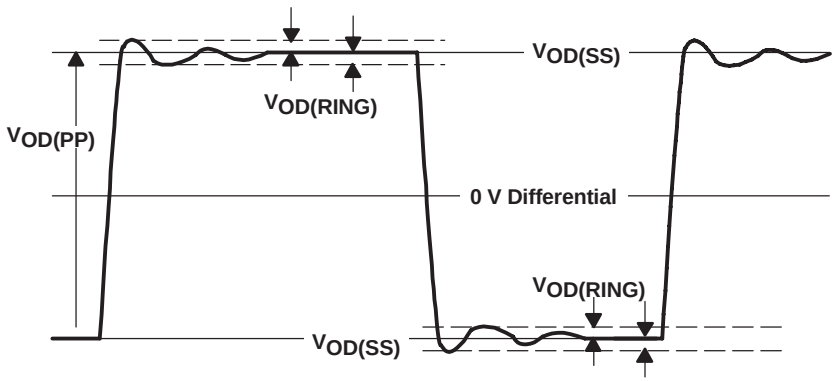


Figure 5. Driver V_{OC} Test Circuit and Waveforms



NOTE: $V_{OD(RING)}$ is measured at four points on the output waveform, corresponding to overshoot and undershoot from the $V_{OD(H)}$ and $V_{OD(L)}$ steady state values.

Figure 6. $V_{OD(RING)}$ Waveform and Definitions

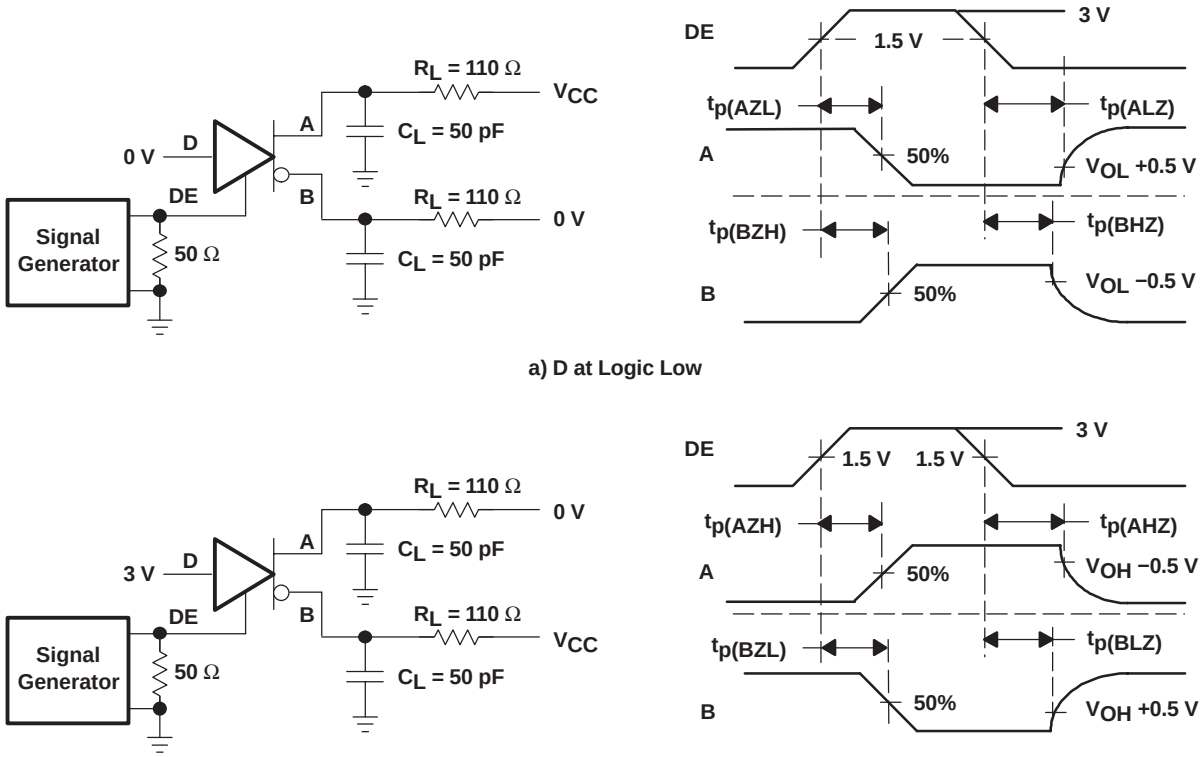


Figure 7. Driver Enable/Disable Test

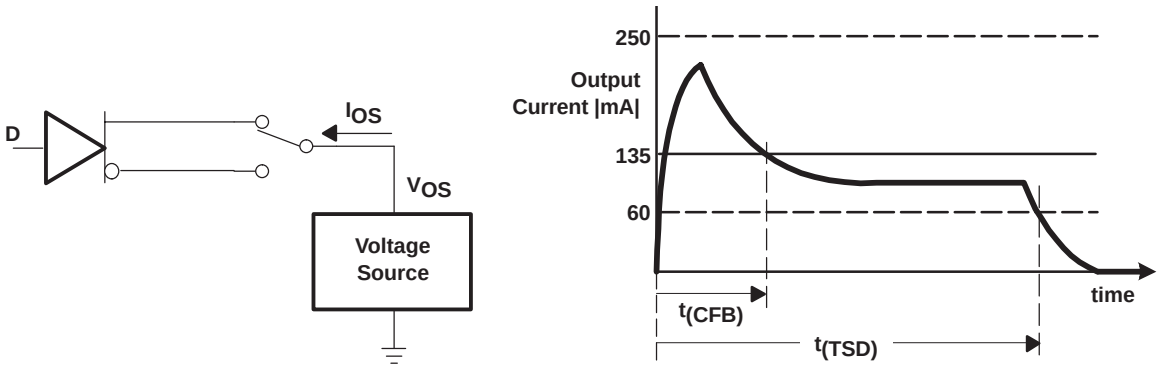


Figure 8. Driver Short-Circuit Test Circuit and Waveforms (Short Circuit applied at Time t = 0)

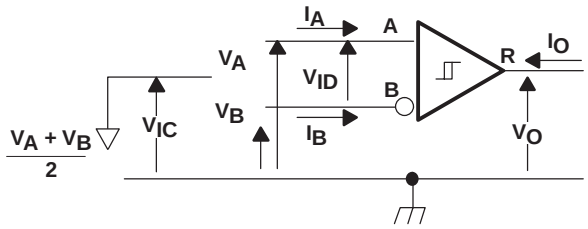


Figure 9. Receiver DC Parameter Definitions

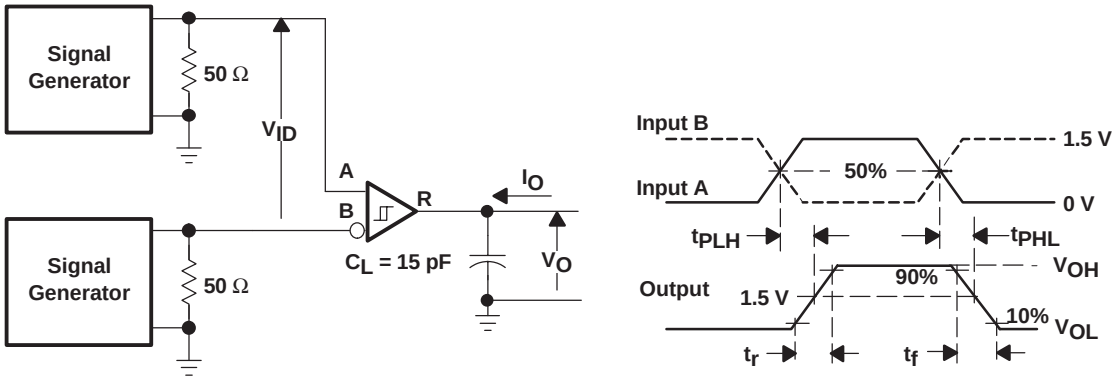


Figure 10. Receiver Switching Test Circuit and Waveforms

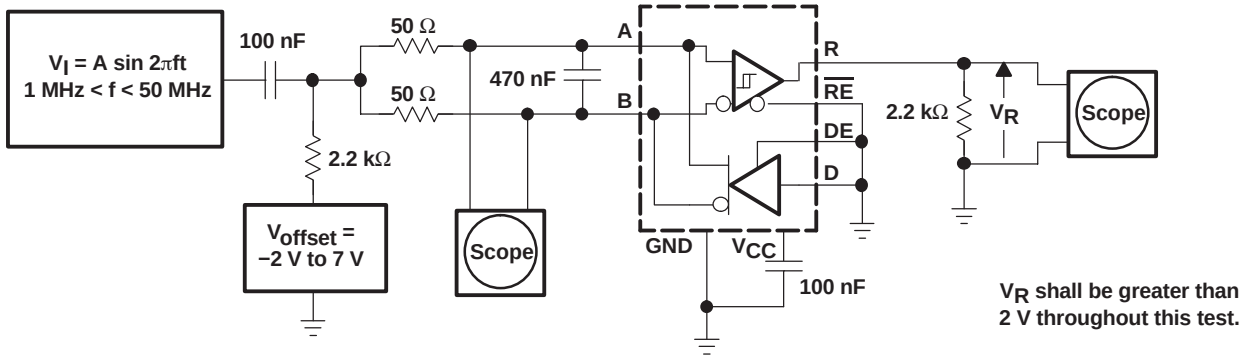


Figure 11. Receiver Common-Mode Rejection Test Circuit

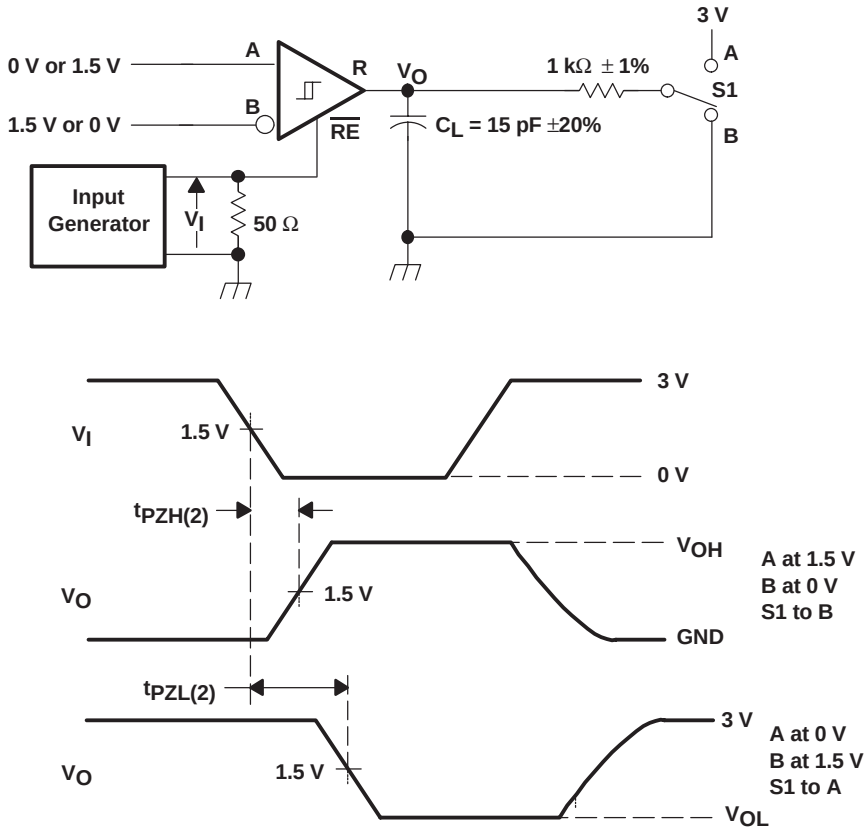


Figure 12. Receiver Enable Time From Standby (Driver Disabled)

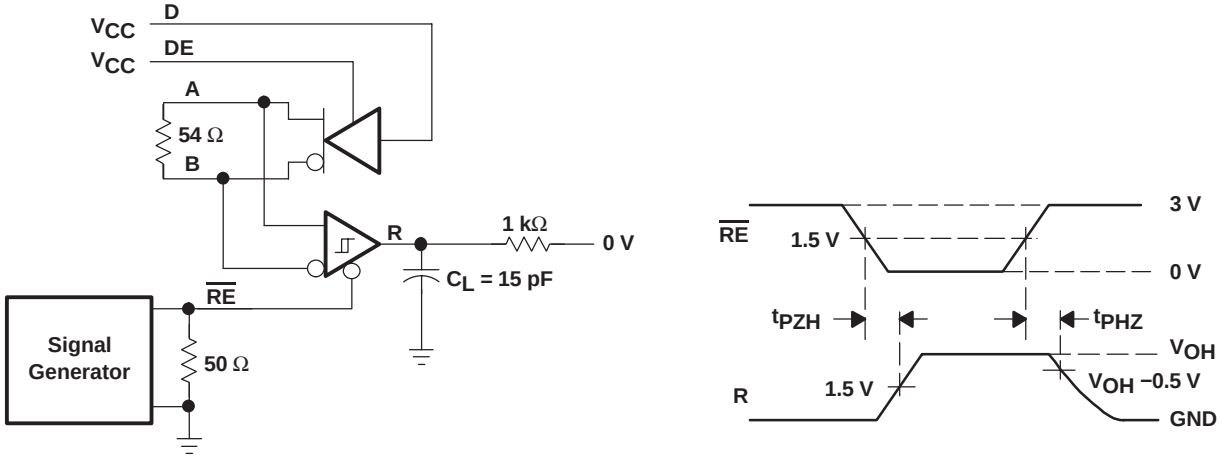


Figure 13. Receiver Enable Test Circuit and Waveforms, Data Output High (Driver Active)

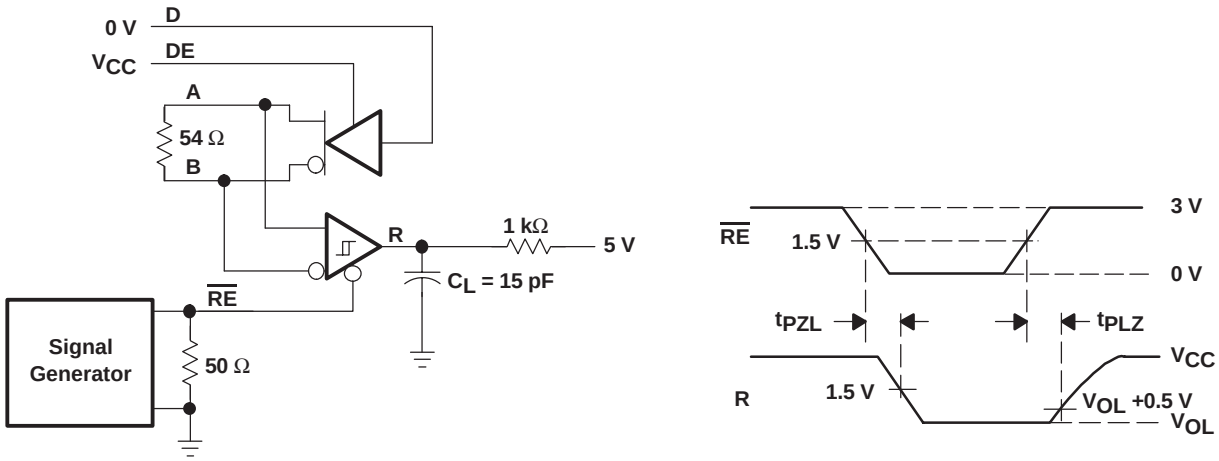


Figure 14. Receiver Enable Test Circuit and Waveforms, Data Output Low (Driver Active)

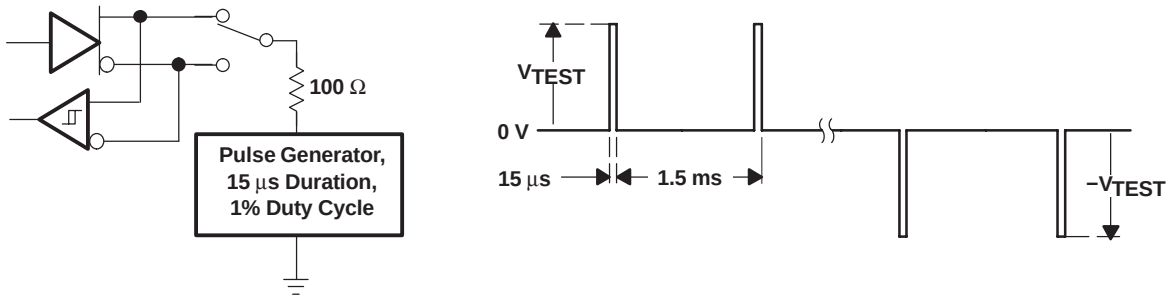


Figure 15. Test Circuit and Waveforms, Transient Over-Voltage Test

DEVICE INFORMATION

DRIVER FUNCTION TABLE			
INPUT	ENABLE	OUTPUTS	
D	DE	A	B
H	H	H	L
L	H	L	H
X	L	Z	Z
X	OPEN	Z	Z
OPEN	H	H	L

H = high level, L= low level, X = don't care,
Z = high impedance (off)

RECEIVER FUNCTION TABLE		
DIFFERENTIAL INPUT $V_{ID} = (V_A - V_B)$	ENABLE $\overline{RE}$	OUTPUT R
$V_{ID} \geq 0.02$ V	L	H
-0.2 V $< V_{ID} < -0.02$ V	L	?
$V_{ID} \leq -0.2$ V	L	L
X	H	Z
X	OPEN	Z
Open circuit	L	H
Short Circuit	L	H
Idle (terminated) bus	L	H

H = high level, L= low level, X = don't care,Z = high impedance (off),
? = indeterminate

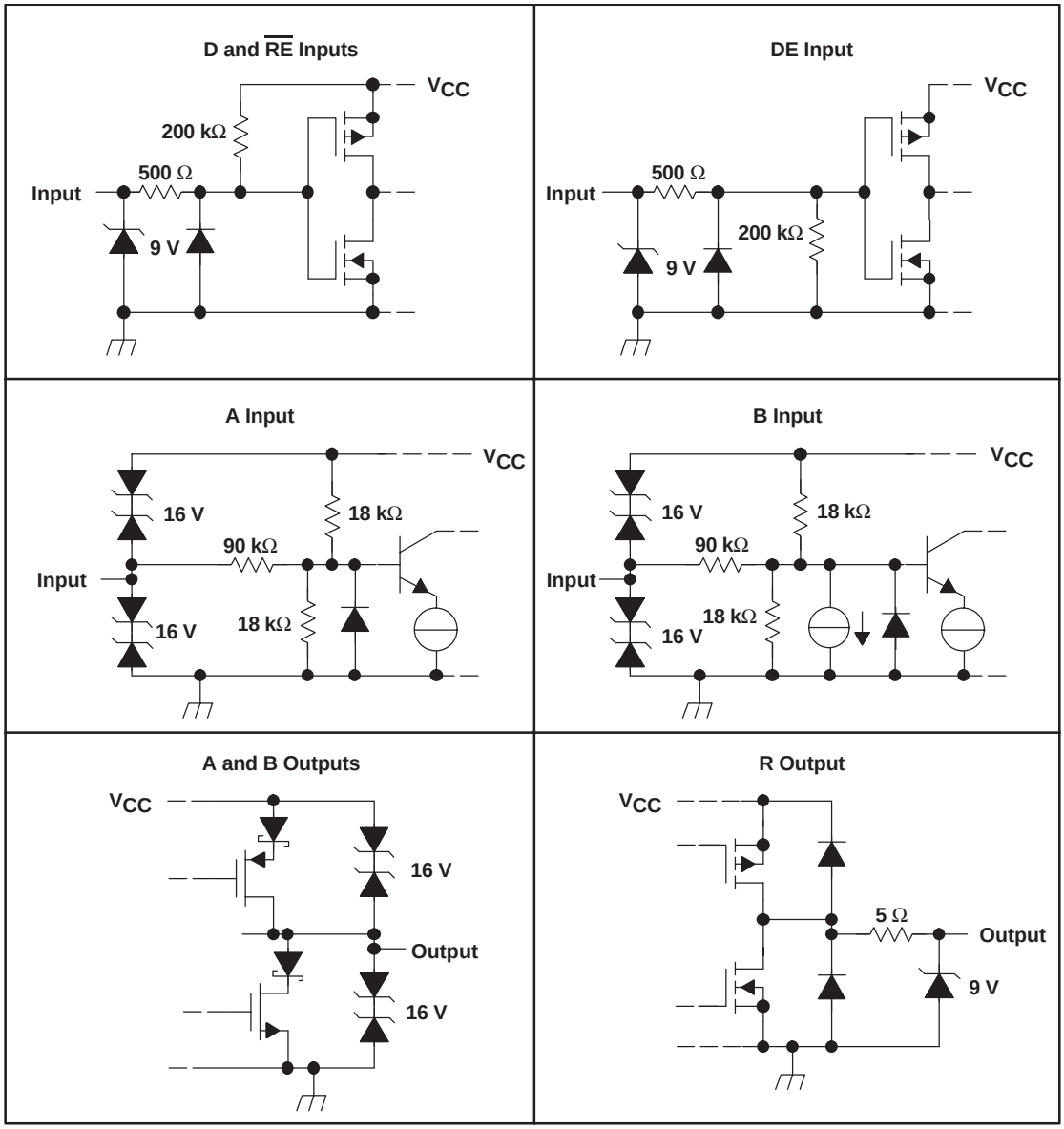
THERMAL CHARACTERISTICS(1)

over recommended operating conditions (unless otherwise noted)

PARAMETERS			TEST CONDITIONS	MIN	TYP(2)	MAX	UNITS
θ_{JA}	Junction-to-ambient thermal resistance(3)		Low-K board(4), no air flow		208.3		°C/W
			High-K board(5), no air flow		128.7		°C/W
θ_{JB}	Junction-to-board thermal resistance		High-K board		77.6		°C/W
θ_{JC}	Junction-to-case thermal resistance				43.9		°C/W
P_D	Device power dissipation		R_L = 54 Ω, C_L= 50 pF, 0 V to 3 V 15 MHz, 50% duty cycle square wave input, driver and receiver enabled		277	318	mW
T_A	Ambient air temperature	SN65HVD1176	Low-K board, no air flow, P_D = 318 mW	−40		64	°C
		SN75HVD1176		0			
		SN65HVD1176	High-K board, no air flow, P_D = 318 mW	−40		89	°C
		SN75HVD1176		0			
T_{SD}	Thermal shut down junction temperature				150		°C

(1) See *Application Information* section for an explanation of these parameters.
(2) All typical values are with V_{CC} = 5 V and T_A = 25°C.
(3) The intent of θ_{JA} specification is solely for a thermal performance comparison of one package to another in a standardized environment. This methodology is not meant to and will not predict the performance of a package in an application-specific environment.
(4) JESD51−3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages.
(5) JESD51−7, High Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages.

EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS



TYPICAL CHARACTERISTICS

DIFFERENTIAL OUTPUT VOLTAGE vs LOAD CURRENT

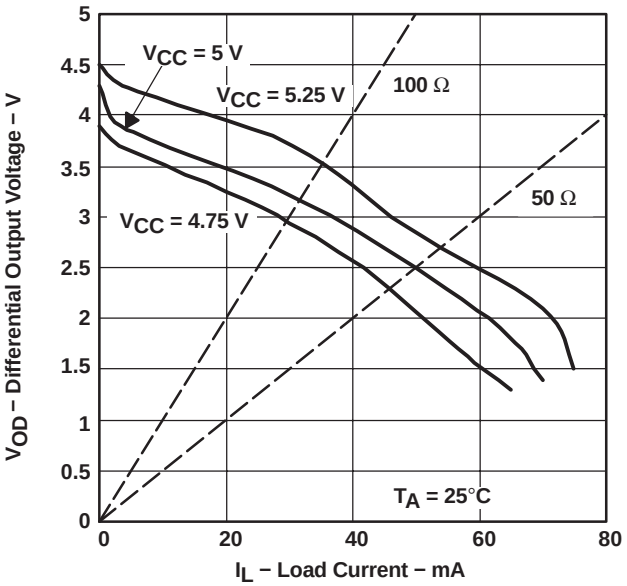


Figure 16

DRIVER SUPPLY CURRENT vs SIGNALING RATE

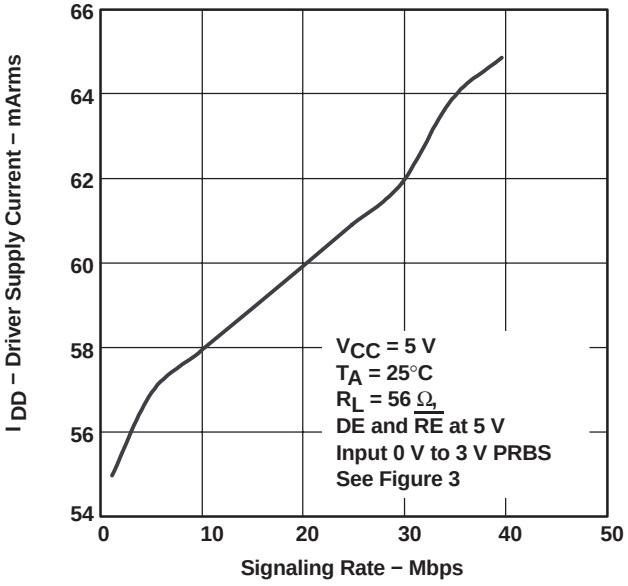


Figure 17

DRIVER OUTPUT TRANSITION SKEW vs FREE-AIR TEMPERATURE

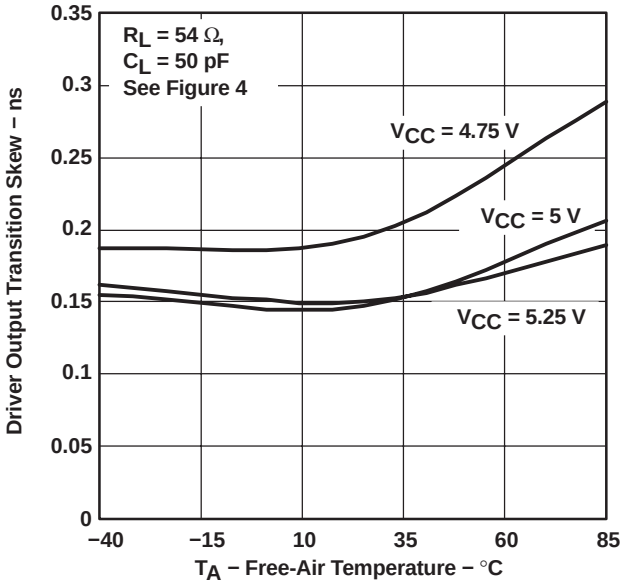


Figure 18

DRIVER RISE, FALL TIME vs FREE-AIR TEMPERATURE

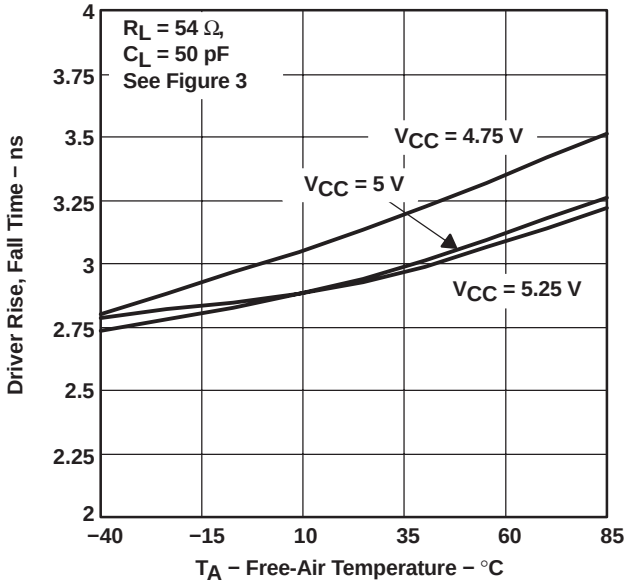


Figure 19

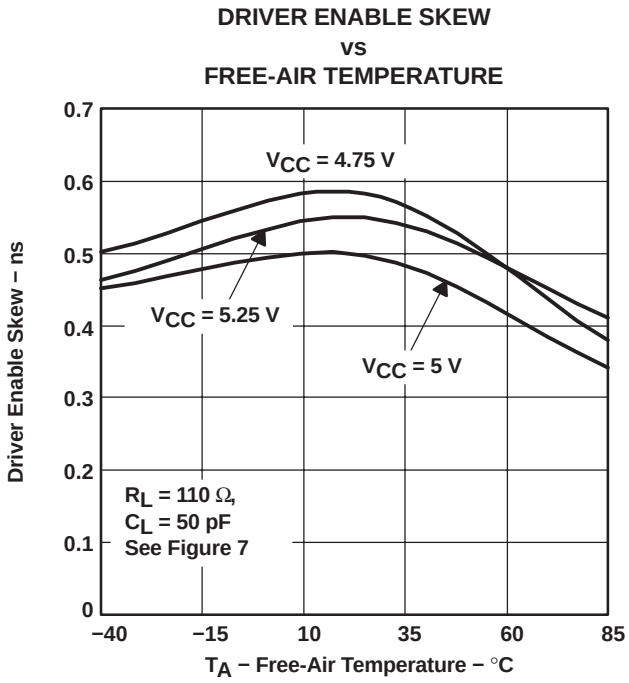


Figure 20

APPLICATION INFORMATION

THERMAL CHARACTERISTICS OF IC PACKAGES

θ_{JA} **(Junction-to-Ambient Thermal Resistance)** is defined as the difference in junction temperature to ambient temperature divided by the operating power.

θ_{JA} is *not* a constant and is a strong function of:

- the PCB design (50% variation)
- altitude (20% variation)
- device power (5% variation)

θ_{JA} can be used to compare the thermal performance of packages if the specific test conditions are defined and used. Standardized testing includes specification of PCB construction, test chamber volume, sensor locations, and the thermal characteristics of holding fixtures. θ_{JA} is often misused when it is used to calculate junction temperatures for other installations.

TI uses two test PCBs as defined by JEDEC specifications. The low-k board gives *average* in-use condition thermal performance, and it consists of a single copper trace layer 25 mm long and 2-oz thick. The high-k board gives *best case* in-use condition, and it consists of two 1-oz buried power planes with a single copper trace layer 25 mm long and 2-oz thick. A 4% to 50% difference in θ_{JA} can be measured between these two test cards

θ_{JC} **(Junction-to-Case Thermal Resistance)** is defined as difference in junction temperature to case divided by the operating power. It is measured by putting the mounted package up against a copper block cold plate to force heat to flow from die, through the mold compound into the copper block.

θ_{JC} is a useful thermal characteristic when a heatsink is applied to package. It is *not* a useful characteristic to predict junction temperature because it provides pessimistic numbers if the case temperature is measured in a nonstandard system and junction temperatures are backed out. It can be used with θ_{JB} in 1-dimensional thermal simulation of a package system.

θ_{JB} (Junction-to-Board Thermal Resistance) is defined as the difference in the junction temperature and the PCB temperature at the center of the package (closest to the die) when the PCB is clamped in a cold-plate structure. θ_{JB} is only defined for the high-k test card.

θ_{JB} provides an overall thermal resistance between the die and the PCB. It includes a bit of the PCB thermal resistance (especially for BGA's with thermal balls) and can be used for simple 1-dimensional network analysis of package system (see Figure 21).

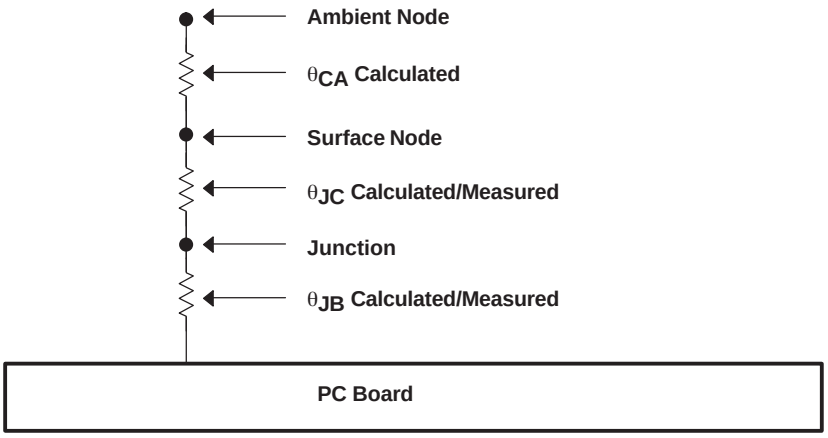


Figure 21. Thermal Resistance

PACKAGING INFORMATION

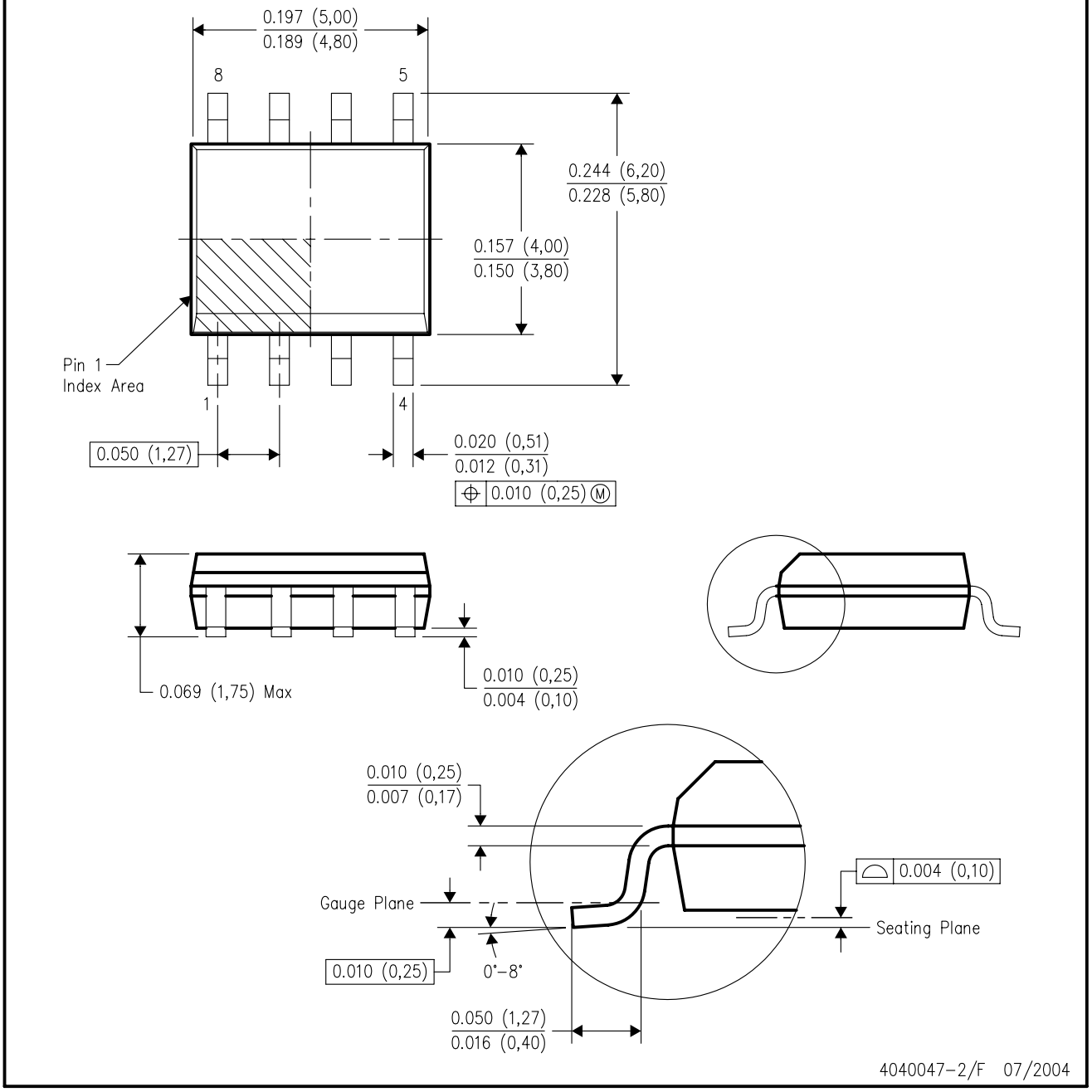
Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
SN65HVD1176D	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
SN65HVD1176DR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
SN75HVD1176D	ACTIVE	SOIC	D	8	75	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM
SN75HVD1176DR	ACTIVE	SOIC	D	8	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1YEAR/ Level-1-220C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - May not be currently available - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
None: Not yet available Lead (Pb-Free).
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Green (RoHS & no Sb/Br): TI defines "Green" to mean "Pb-Free" and in addition, uses package materials that do not contain halogens, including bromine (Br) or antimony (Sb) above 0.1% of total product weight.

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDECindustry standard classifications, and peak solder temperature.

D (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–012 variation AA.

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		**Applications**	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
		Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments
Post Office Box 655303 Dallas, Texas 75265